

MMBT4126LT1G

General Purpose Transistor

PNP Silicon

Features

- Moisture Sensitivity Level: 1
- ESD Rating: – Human Body Model: > 4000 V
– Machine Model: > 400 V
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	–25	Vdc
Collector–Base Voltage	V_{CBO}	–25	Vdc
Emitter–Base Voltage	V_{EBO}	–4	Vdc
Collector Current–Continuous	I_C	–200	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board (Note 1) @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient (Note 1)	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient (Note 2)	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	T_J, T_{stg}	–55 to +150	$^\circ\text{C}$

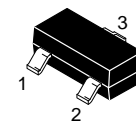
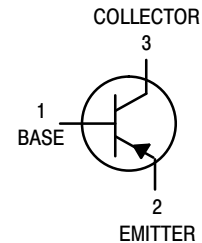
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR–5 = $1.0 \times 0.75 \times 0.062$ in.
2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.



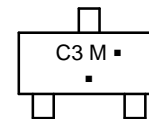
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SOT–23
CASE 318
STYLE 6

MARKING DIAGRAM



C3 = Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)
*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMBT4126LT1G	SOT–23 (Pb–Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage (Note 3) ($I_C = -1.0\text{ mA}$, $I_B = 0$)	$V_{(BR)CEO}$	-25	-	Vdc
Collector–Base Breakdown Voltage ($I_C = -10\text{ }\mu\text{A}$, $I_E = 0$)	$V_{(BR)CBO}$	-25	-	Vdc
Emitter–Base Breakdown Voltage ($I_E = -10\text{ }\mu\text{A}$, $I_C = 0$)	$V_{(BR)EBO}$	-4	-	Vdc
Collector Cutoff Current ($V_{CE} = -30\text{ Vdc}$, $V_{EB} = -3.0\text{ Vdc}$)	I_{CEX}	-	-50	nAdc
ON CHARACTERISTICS (Note 3)				
DC Current Gain ($I_C = -2.0\text{ mA}$, $V_{CE} = -1.0\text{ Vdc}$) ($I_C = -50\text{ mA}$, $V_{CE} = -1.0\text{ Vdc}$)	H_{FE}	120 60	300 -	-
Collector–Emitter Saturation Voltage ($I_C = -50\text{ mA}$, $I_B = -5.0\text{ mA}$)	$V_{CE(sat)}$	-	-0.4	Vdc
Base–Emitter Saturation Voltage ($I_C = -50\text{ mA}$, $I_B = -5.0\text{ mA}$)	$V_{BE(sat)}$	-	-0.95	Vdc
SMALL–SIGNAL CHARACTERISTICS				
Current–Gain – Bandwidth Product ($I_C = -10\text{ mA}$, $V_{CE} = -20\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	250	-	MHz
Output Capacitance ($V_{CB} = -5.0\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{obo}	-	4.5	pF
Input Capacitance ($V_{EB} = -0.5\text{ Vdc}$, $I_C = 0$, $f = 1.0\text{ MHz}$)	C_{ibo}	-	10	pF
Small–Signal Current Gain ($I_C = -2.0\text{ mA}$, $V_{CE} = -10\text{ Vdc}$, $f = 1.0\text{ kHz}$) ($I_C = 10\text{ mA}$, $V_{CE} = 20\text{ Vdc}$, $f = 100\text{ MHz}$)	h_{fe}	120 2.5	480 -	-
Noise Figure ($I_C = -100\text{ }\mu\text{A}$, $V_{CE} = -5.0\text{ Vdc}$, $R_S = 1.0\text{ k}\Omega$, $f = 1.0\text{ kHz}$)	NF	-	4.0	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$.

TYPICAL TRANSIENT CHARACTERISTICS

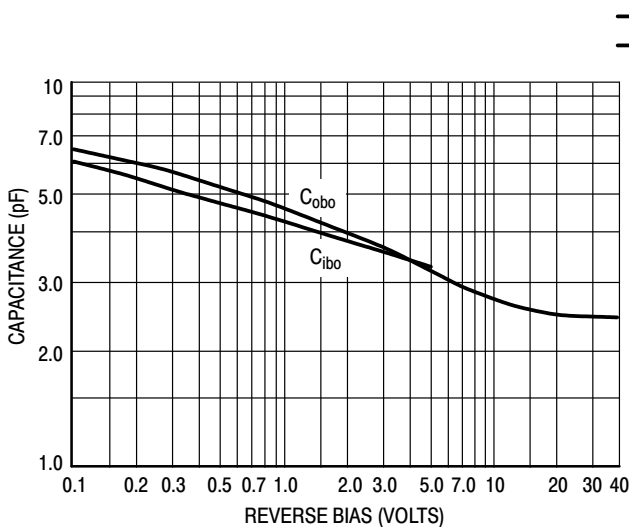


Figure 1. Capacitance

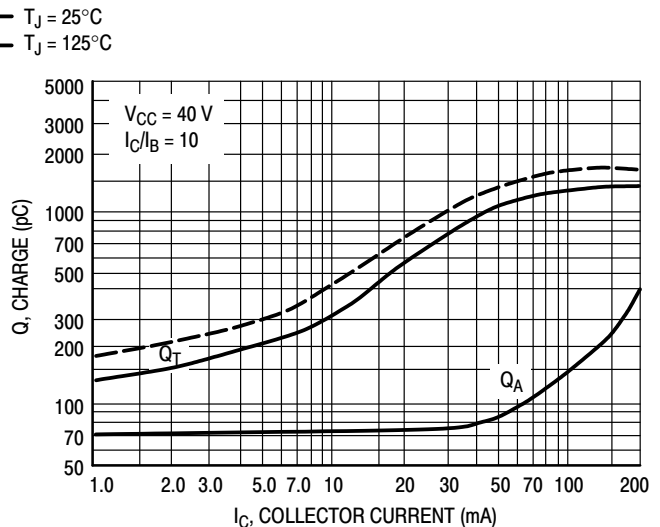


Figure 2. Charge Data

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TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

($V_{CE} = -5.0$ Vdc, $T_A = 25^\circ\text{C}$, Bandwidth = 1.0 Hz)

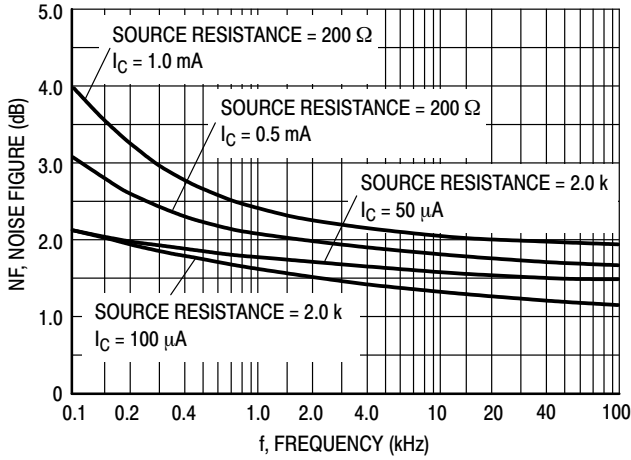


Figure 3.

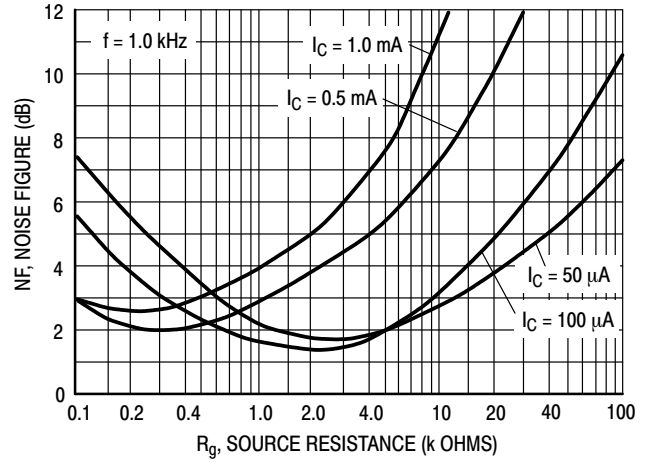


Figure 4.

h PARAMETERS

($V_{CE} = -10$ Vdc, $f = 1.0$ kHz, $T_A = 25^\circ\text{C}$)

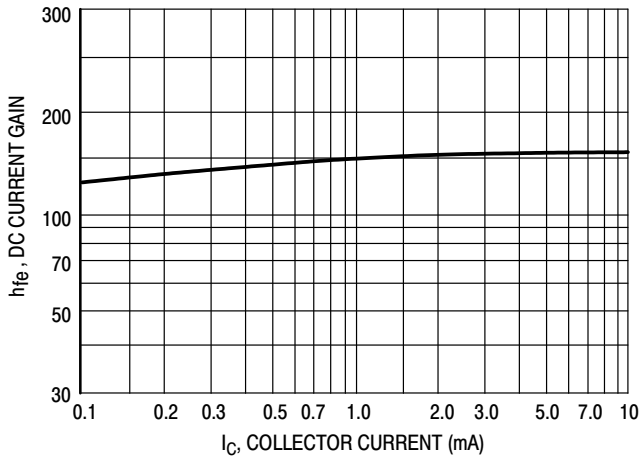


Figure 5. Current Gain

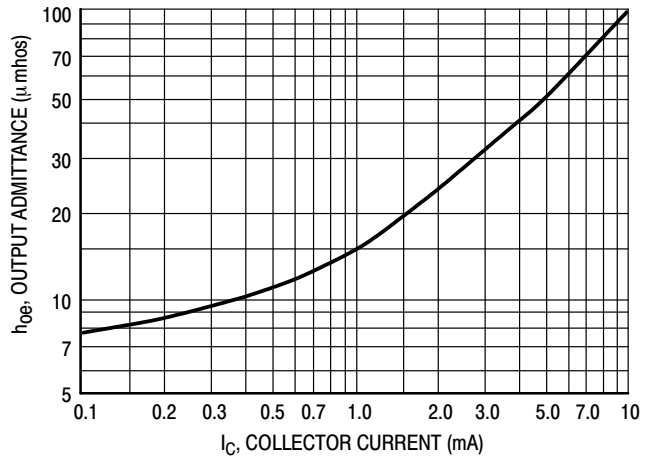


Figure 6. Output Admittance

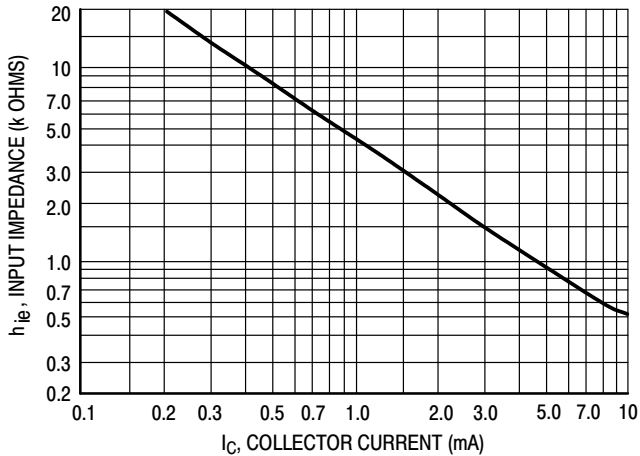


Figure 7. Input Impedance

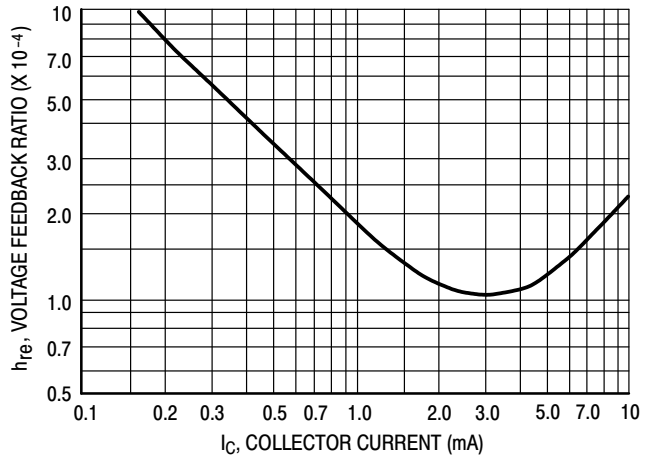


Figure 8. Voltage Feedback Ratio

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TYPICAL STATIC CHARACTERISTICS

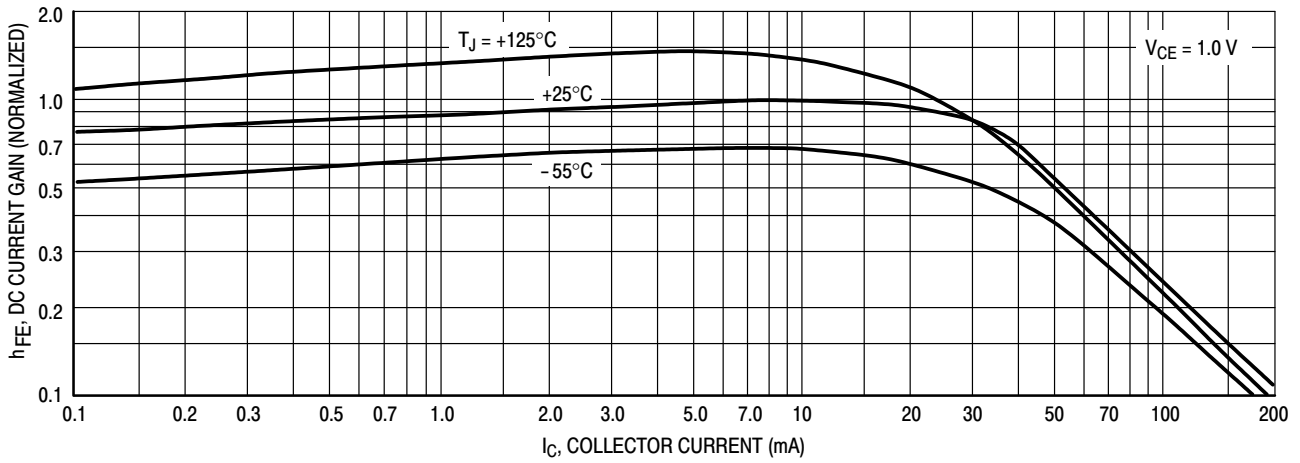


Figure 9. DC Current Gain

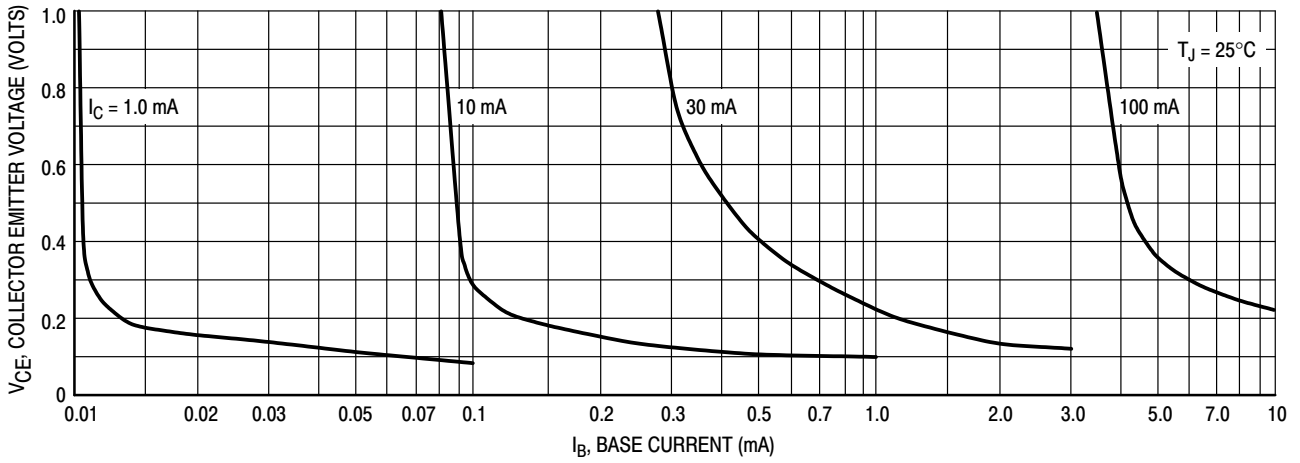


Figure 10. Collector Saturation Region

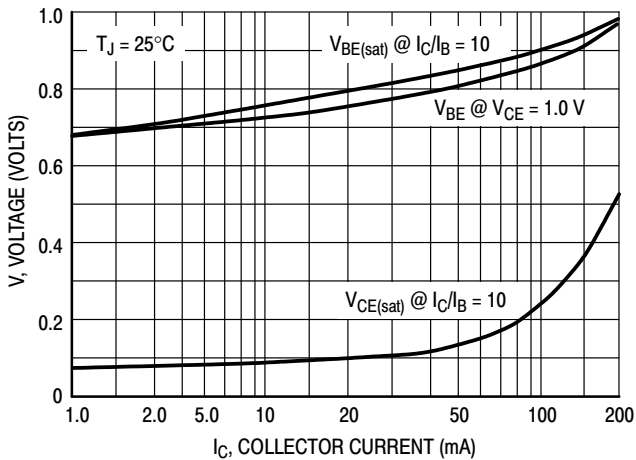


Figure 11. "ON" Voltages

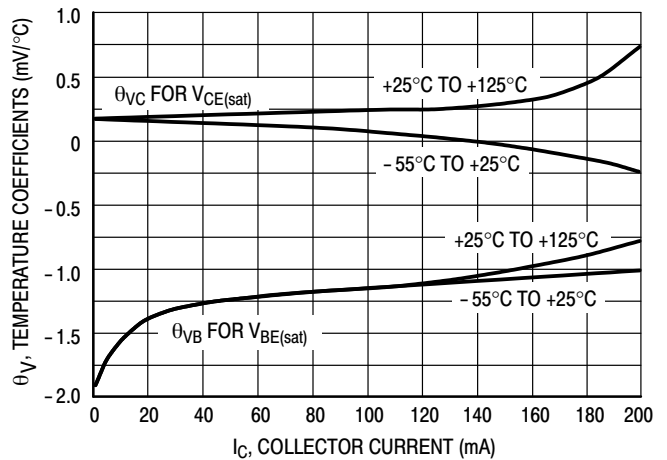


Figure 12. Temperature Coefficients

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

ON Semiconductor®



SOT-23 (TO-236) CASE 318-08 ISSUE AS

DATE 30 JAN 2018

SCALE 4:1



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

RECOMMENDED SOLDERING FOOTPRINT



GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

STYLE 1 THRU 5:
CANCELLED

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE-ANODE

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE

STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE

STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE-ANODE

STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT

STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE

STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION

STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE

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